描述 / Descriptions

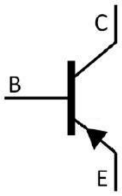
TO-92 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a TO-92 Plastic Package.

特征 / Features 用途 / Applications

低电流，低电压。用于一般放大。

Low current, Low voltage.
General purpose amplifier.

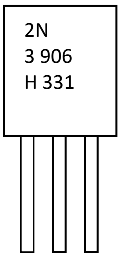
内部等效电路 / Equivalent Circuit 引脚排列 / Pinning



PIN1：Collector PIN 2：Base PIN 3：Emitter

放大及印章代码 / hFE Classifications & Marking

*HFE(1)分档及打印

分 档	1					印记见下 **具体内容以打印为准**
HFE(1)	100~300					
打印（简例）						
其 它 说 明	封装外形：TO-92 管脚排列： E、B、C					

极限参数 / Absolute Maximum Ratings(Ta=25℃)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

电性能参数 / Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-10μA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-40			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-10μA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-40V I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-1.0V I_C=-10mA	100		300	
	$h_{FE(2)}$	V_{CE}=-1.0V I_C=-100mA	30			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-50mA I_B=-5.0mA			-0.4	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-50mA I_B=-5.0mA			-0.95	V
Current Gain Bandwidth Product	f_T	I_C=-10mA V_{CE}=-20V f=100MHz	250			MHz
Output Capacitance	C_{ob}	V_{CB}=-5.0V I_E=0 f=100KHz			4.5	pF
Turn On Time	T_{on}	V_{CC}=-3.0V I_C=-10mA V_{BE}=-0.5V I_{B1}=-1.0mA			0.07	μs
Turn Off Time	T_{off}	V_{CC}=-3.0V I_C=-10mA I_{B1}=-I_{B2}=-1.0mA			0.3	μs

电参数曲线图 / Electrical Characteristic Curve